Data sheet acquired from Harris Semiconductor SCHS133A

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# **建**多邦, 专业PCB打样エ厂 **CD54/74**HC42, **CD74HCT42**

# High Speed CMOS Logic BCD To Decimal Decoder (1 of 10)

#### Features

- . Buffered Inputs and Outputs
- Typical Propagation Delay: 12ns at V<sub>CC</sub> = 5V, C<sub>L</sub> = 15pF, T<sub>A</sub> = 25°C
- Fanout (Over Temperature Range)
  - Standard Outputs..... 10 LSTTL Loads
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N<sub>IL</sub> = 30%, N<sub>IH</sub> = 30% of V<sub>CC</sub> at V<sub>CC</sub> = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,
     V<sub>IL</sub>= 0.8V (Max), V<sub>IH</sub> = 2V (Min)
  - CMOS Input Compatibility,  $I_{I} \leq 1 \mu A$  at  $V_{OL},\,V_{OH}$

# Description

The 'HC42 and CD74HCT42 BCD-to-Decimal Decoders utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL decoders with the low power consumption of standard CMOS integrated circuits. These devices have the capability of driving 10 LSTLL loads and are compatible with the standard LS logic family. One of ten outputs (low on select) is selected in accordance with the BCD input. Non-valid BCD inputs result in none of the outputs being selected (all outputs are high).

# Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE				
CD54HC42F3A	-55 to 125	16 Ld CERDIP				
CD74HC42E	-55 to 125	16 Ld SOIC				
CD74HC42M	-55 to 125	16 Ld SOIC				
CD74HCT42E	-55 to 125	16 Ld PDIP				

#### NOTES:

- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- Die for this part number is available which meets all electrical specifications. Please contact your local TI sales office or customer service for ordering information.

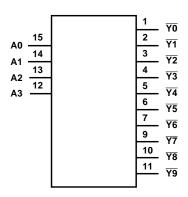
# **Pinout**

CD54HC42 (CERDIP) CD74HC42, CD74HCT42 (PDIP, SOIC) TOP VIEW





# Functional Diagram



# TRUTH TABLE

	INP	UTS						OUTI	PUTS				
А3	A2	A1	A0	Y0	<u>Y1</u>	Y2	<u></u> 73	<b>Y</b> 4	<u>Y5</u>	<u>Y6</u>	<b>Y7</b>	<u>78</u>	<u> 79</u>
L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н
L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н
L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н	Н	Н
L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	Н
L	Н	L	L	Н	Н	Н	Н	L	Н	Н	Н	Н	Н
L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н	Н	Н
L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н	Н
L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	Н
Н	L	L	L	Н	Н	Н	Н	Н	Н	Н	Н	L	Н
Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L
Н	L	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
Н	Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н

NOTE: H = High Voltage Level, L = Low Voltage Level

# Absolute Maximum Ratings DC Supply Voltage, $V_{CC}$ ... -0.5V to 7V DC Input Diode Current, $I_{IK}$ For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ ... $\pm 20$ mA DC Output Diode Current, $I_{OK}$ For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ ... $\pm 20$ mA DC Output Source or Sink Current per Output Pin, $I_O$ For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ ... $\pm 25$ mA DC $V_{CC}$ or Ground Current, $I_{CC}$ or $I_{GND}$ ... $\pm 25$ mA Operating Conditions Temperature Range $(T_A)$ ... $-55^{\circ}$ C to $125^{\circ}$ C

 HC Types
 .2V to 6V

 HCT Types
 .4.5V to 5.5V

 DC Input or Output Voltage, V<sub>I</sub>, V<sub>O</sub>
 .0V to V<sub>CC</sub>

 2V
 1000ns (Max)

 4.5V
 500ns (Max)

 6V
 400ns (Max)

#### **Thermal Information**

Thermal Resistance (Typical, Note 3)	θ <sub>JA</sub> (°C/W)
PDIP Package	90
SOIC Package	190
Maximum Junction Temperature	
Maximum Storage Temperature Range	65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

3.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

## **DC Electrical Specifications**

Supply Voltage Range,  $V_{CC}$ 

Input Rise and Fall Time

		TE: CONDI	_	V <sub>CC</sub>	25 <sup>0</sup> C			-40°C 1	O 85°C	-55°C TO 125°C		
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES												
High Level Input	V <sub>IH</sub>	-	-	2	1.5	-	-	1.5	-	1.5	-	٧
Voltage				4.5	3.15	•	-	3.15	-	3.15	-	<b>V</b>
				6	4.2	ı	-	4.2	-	4.2	-	V
Low Level Input	V <sub>IL</sub>	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output	VoH	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
Voltage CMOS Loads			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
OWOO LOAGS			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output			-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
TTE LOAGS			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	2	-	-	0.1	-	0.1	-	0.1	V
Voltage CMOS Loads			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
OWOO LOAGS			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output			-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
I I L Loaus			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	II	V <sub>CC</sub> or GND	-	6	-	-	±0.1	-	±1	-	±1	μΑ
Quiescent Device Current	lcc	V <sub>CC</sub> or GND	0	6	-	ı	8	-	80	-	160	μΑ

# DC Electrical Specifications (Continued)

		TEST CONDITIONS		v <sub>cc</sub>	25°C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	(S)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HCT TYPES												
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lį	V <sub>CC</sub> and GND	0	5.5	-		±0.1	-	±1	-	±1	μА
Quiescent Device Current	Icc	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	μА
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	Δl <sub>CC</sub>	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μΑ

NOTE: For dual-supply systems theoretical worst case ( $V_I = 2.4V$ ,  $V_{CC} = 5.5V$ ) specification is 1.8mA.

# **HCT Input Loading Table**

INPUT	UNIT LOADS
All	1

NOTE: Unit Load is  $\Delta I_{\hbox{CC}}$  limit specified in DC Electrical Table, e.g. 360µA max at 25  $^{\rm o}$ C.

# Switching Specifications Input $t_{\text{r}},\,t_{\text{f}}=6\text{ns}$

		TEST		25°C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	SYMBOL	CONDITIONS	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES	•										
Propagation Delay,	t <sub>PLH</sub> , t <sub>PHL</sub>	C <sub>L</sub> = 50pF	2	-	-	150	-	190	-	225	ns
Input to Y (Figure 1)			4.5	-	-	30	-	38	-	45	ns
			6	-	-	26	-	33	-	38	ns
Any Input to $\overline{Y}$	t <sub>PLH</sub> , t <sub>PHL</sub>	C <sub>L</sub> = 15pF	5	-	12	-	-	-	-	-	ns
Output Transition Time	t <sub>TLH</sub> , t <sub>THL</sub>	C <sub>L</sub> = 50pF	2	-	-	75	-	95	-	110	ns
(Figure 1)			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C <sub>IN</sub>	-	-	-	-	10	-	10	-	10	pF

# Switching Specifications Input $t_p$ , $t_f$ = 6ns (Continued)

		TEST		25°C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	SYMBOL	CONDITIONS	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Power Dissipation Capacitance (Notes 4, 5)	C <sub>PD</sub>	-	5	-	65	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay, Input to Y (Figure 2)	t <sub>PLH</sub> , t <sub>PHL</sub>	C <sub>L</sub> = 50pF	4.5	i	-	35	-	44	-	53	ns
Any Input to $\overline{Y}$	t <sub>PLH</sub> , t <sub>PHL</sub>	C <sub>L</sub> = 15pF	5	-	14	-	-	-	-	-	ns
Output Transition Time (Figure 2)	t <sub>TLH</sub> , t <sub>THL</sub>	C <sub>L</sub> = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C <sub>IN</sub>	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C <sub>PD</sub>	-	5	-	70	-	-	-	-	- -	pF

#### NOTES:

- 4.  $C_{\mbox{\scriptsize PD}}$  is used to determine the dynamic power consumption, per package.
- 5.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where:  $f_i = Input$  Frequency,  $C_L = Output$  Load Capacitance,  $V_{CC} = Supply$  Voltage.

# Test Circuits and Waveforms

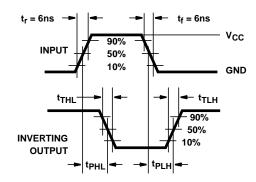


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

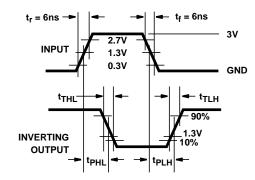


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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